

SKM 22GD123D



SEMITRANS® 6

IGBT modules

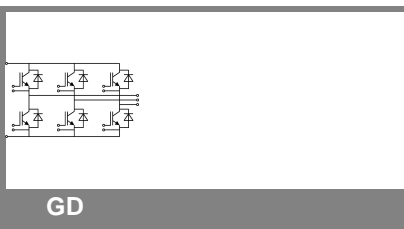
SKM 22GD123D

Features

- MOS input (voltage controlled)
- N channel, homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (9 mm) and creepage distances (13 mm)

Typical Applications*

- Switched mode power supplies
- Three phase inverters for AC motor speed control
- General power switching applications
- Pulse frequencies also above 15 kHz



GD

Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	1200		V
I_C	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	25	A
		$T_{case} = 80^\circ\text{C}$	15	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	50		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		μs
Inverse Diode				
I_F	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	25	A
		$T_{case} = 80^\circ\text{C}$	15	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	50		A
I_{FSM}	$t_p = 10\text{ ms}; \text{sin.}$	$T_j = 150^\circ\text{C}$	200	A
Module				
$I_{t(RMS)}$		100		A
T_{vj}		- 40 ... + 175		$^\circ\text{C}$
T_{stg}		- 40...+ 125		$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_c = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$		0,3	0,9	mA
V_{CE0}		$T_j = 25^\circ\text{C}$	1,4	1,6	V
		$T_j = 125^\circ\text{C}$	1,6	1,8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	73,33	93,33	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$	100	126,66	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 15\text{ A}, V_{GE} = 15\text{ V}$	$T_j = ^\circ\text{C}_{chiplev.}$	2,5	3	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	1		nF
C_{oes}			0,15		nF
C_{res}			0,07		nF
$t_{d(on)}$	$R_{Gon} = 52\ \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 25\text{ A}$	40		ns
t_r			35		ns
E_{on}	$R_{Goff} = 52\ \Omega$	$T_j = 125^\circ\text{C}$ $V_{GE} = -15\text{ V}$	2		mJ
$t_{d(off)}$			350		ns
t_f			70		ns
E_{off}			1,4		mJ
$R_{th(j-c)}$	per IGBT		0,86		K/W



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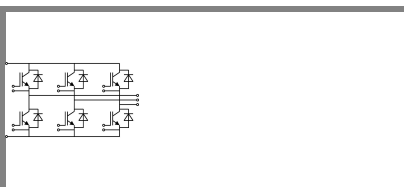
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Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 15 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,8		V
V_{F0}		$T_j = 25 \text{ }^\circ\text{C}$	1,1	1,2	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
r_F		$T_j = 25 \text{ }^\circ\text{C}$	60	87	mΩ
		$T_j = 125 \text{ }^\circ\text{C}$			mΩ
I_{RRM}	$I_F = 15 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$	16		A
Q_{rr}			2,7		μC
E_{rr}	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$		0,95		mJ
$R_{th(j-c)D}$	per diode			1,5	K/W
Module					
L_{CE}				60	nH
$R_{th(c-s)}$	per module			0,05	K/W
M_s	to heat sink M5		4	5	Nm
w				175	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



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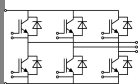
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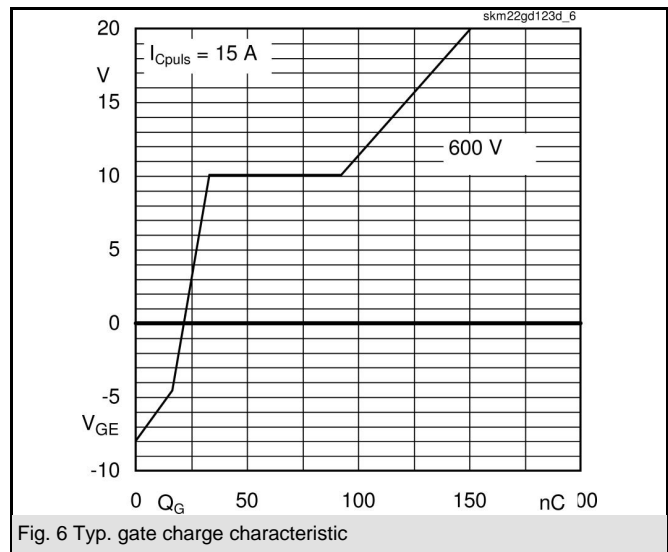
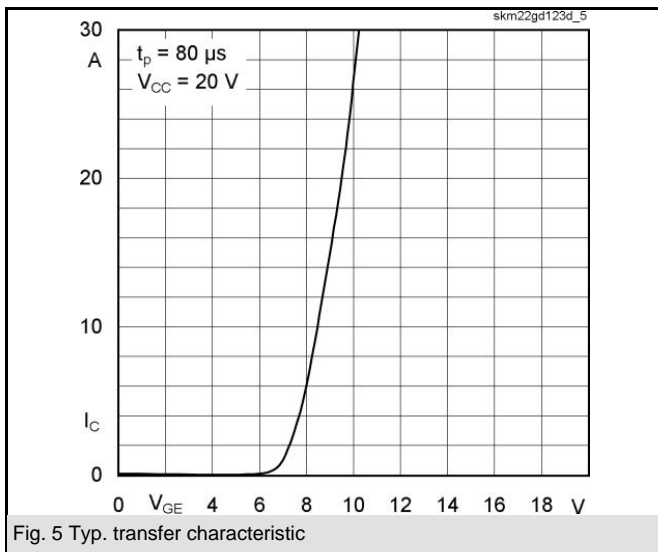
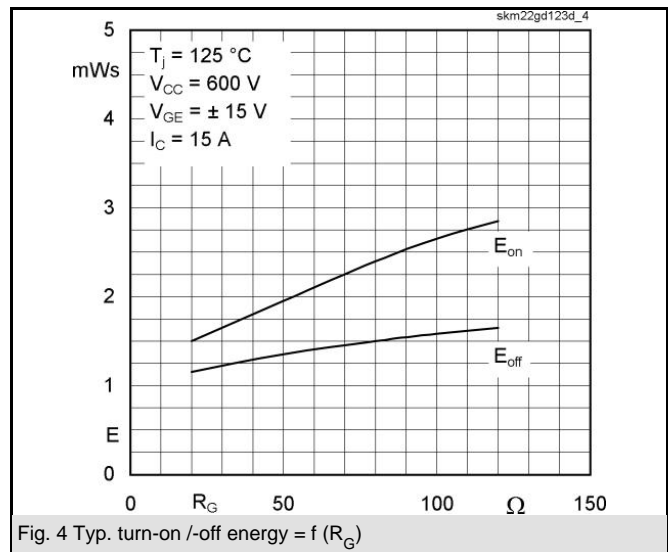
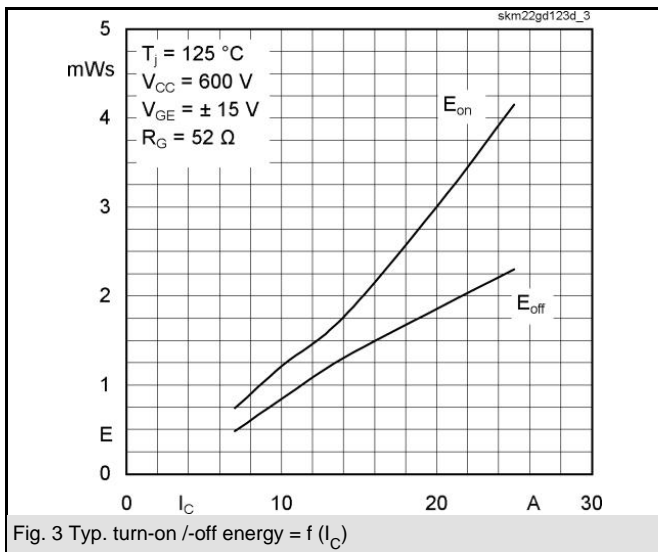
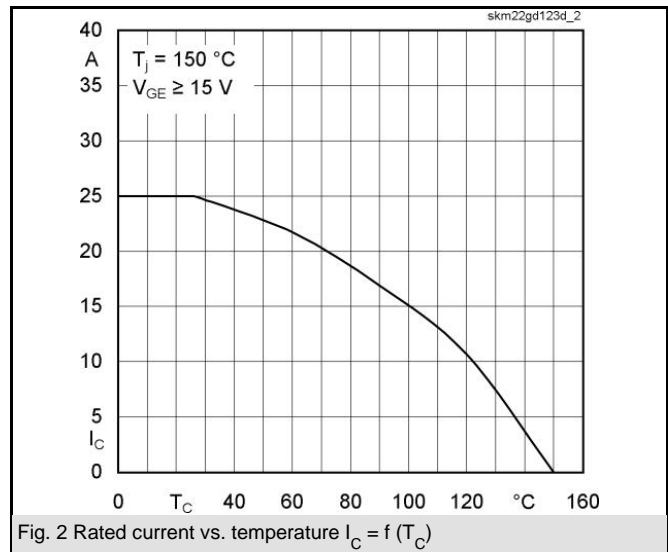
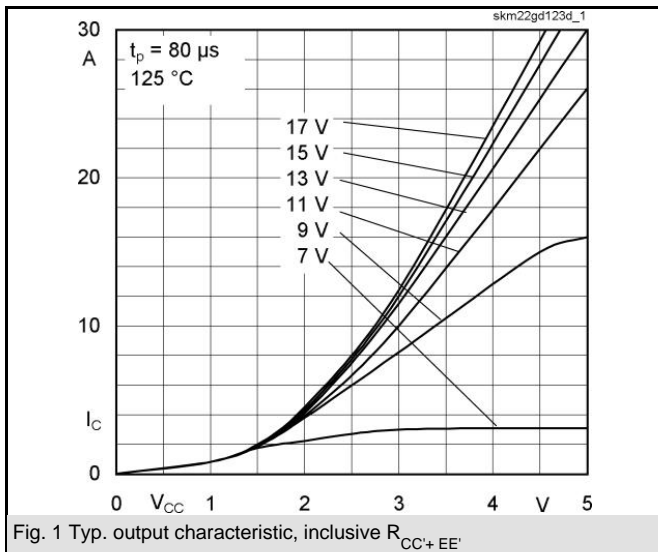
Typical Applications*

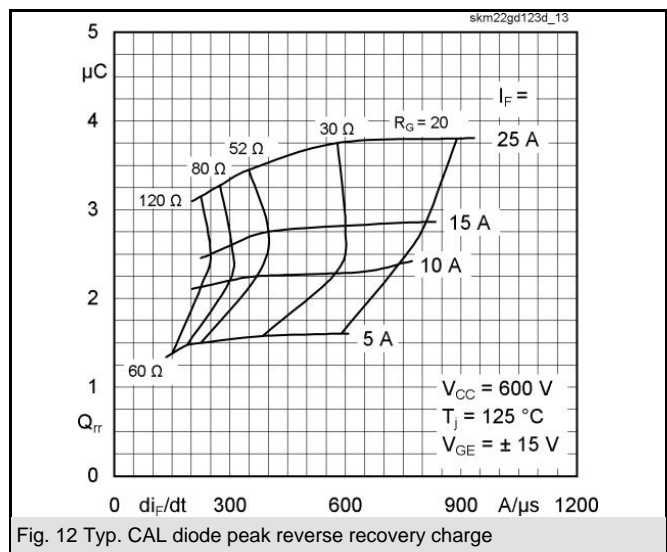
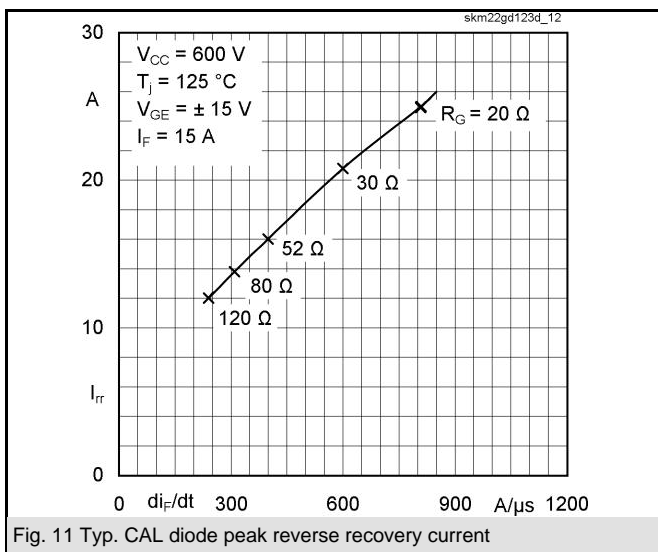
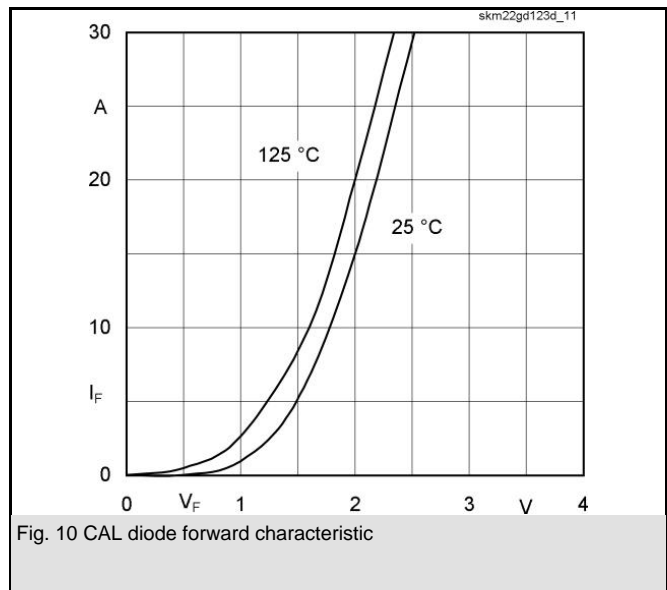
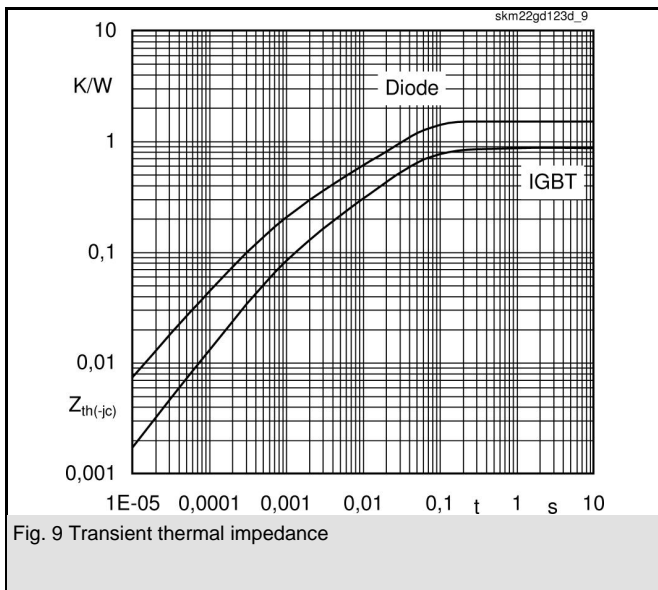
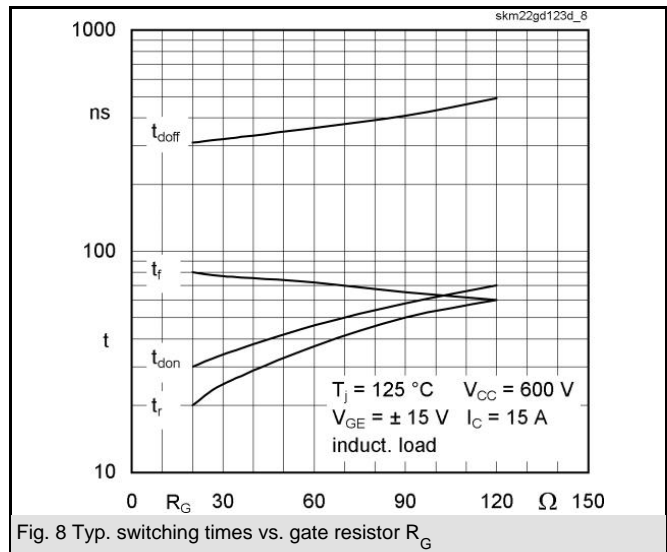
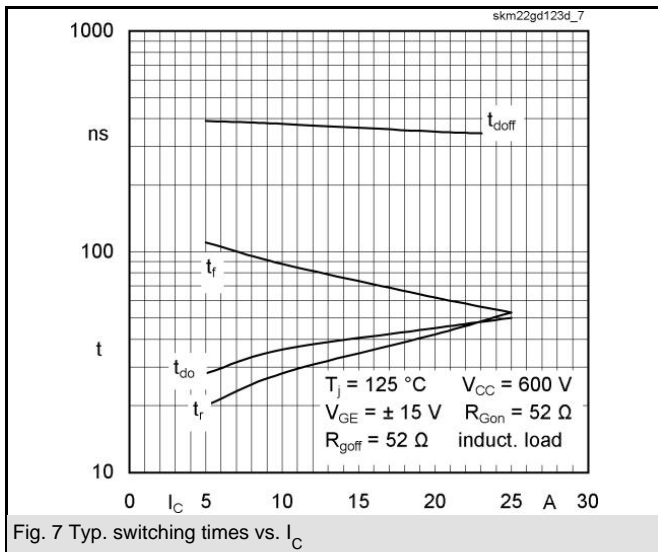
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Z_{th}		Values	Units
Symbol	Conditions		
$Z_{th(j-c)I}$			
R_i	$i = 1$	560	mk/W
R_i	$i = 2$	220	mk/W
R_i	$i = 3$	67	mk/W
R_i	$i = 4$	13	mk/W
τ_{u_i}	$i = 1$	0,056	s
τ_{u_i}	$i = 2$	0,0078	s
τ_{u_i}	$i = 3$	0,017	s
τ_{u_i}	$i = 4$	0,0001	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	800	mk/W
R_i	$i = 2$	400	mk/W
R_i	$i = 3$	270	mk/W
R_i	$i = 4$	30	mk/W
τ_{u_i}	$i = 1$	0,0761	s
τ_{u_i}	$i = 2$	0,0013	s
τ_{u_i}	$i = 3$	0,011	s
τ_{u_i}	$i = 4$	0,002	s



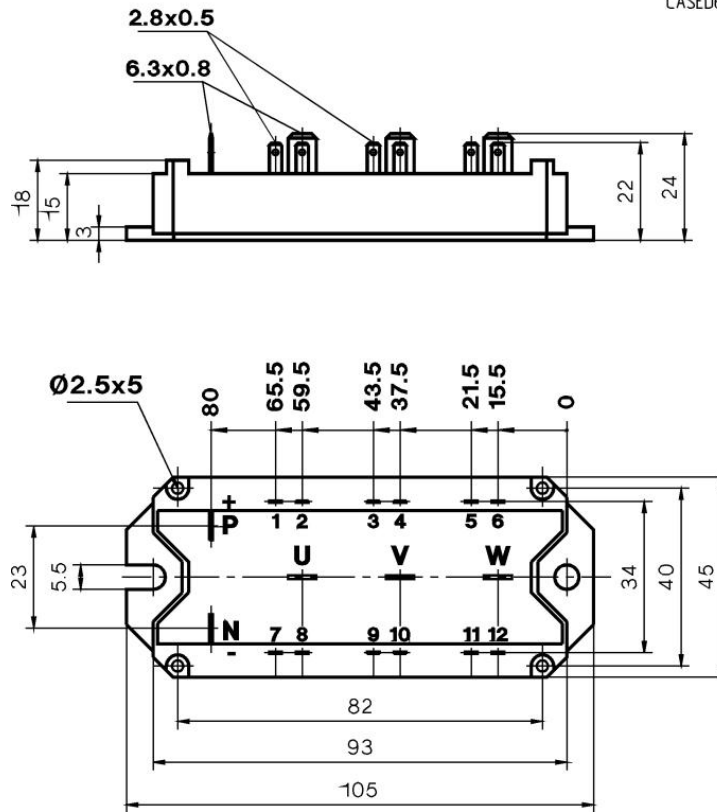


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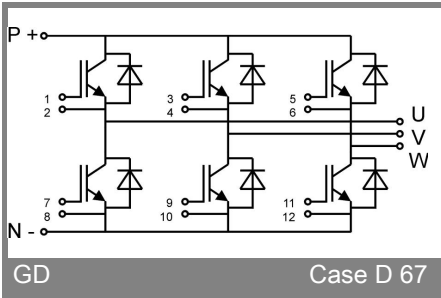
UL Recognized

CASED67

File 63 532



Case D 67



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Case D 67